

# TRANSISTOR (PNP)

#### FEATURES

- For AF driver and output stages
- High collector current
- Low collector-emitter saturation voltage
- Complementary types: BCP54...BCP56 (NPN)



#### MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)

Symbol	Parameter	BCP51	BCP52	BCP53	Units
V <sub>СВО</sub>	Collector-Base Voltage	-45	-60	-100	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-45	-60	-80	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5		V	
lc	Collector Current -Continuous -1		А		
Pc	Collector Power Dissipation 1.5			W	
$R_{\theta JA}$	Thermal Resistance Junction to Ambient 94		°C/W		
T <sub>stg</sub>	Storage Temperature Range	-65to+150		°C	

#### ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter		Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	BCP51			-45		
	BCP52	V <sub>(BR)CBO</sub>	I <sub>C</sub> =- 0.1mA,I <sub>E</sub> =0	-60		V
	BCP53			-100		
Collector-emitter breakdown voltage BCP51				-45		
	BCP52	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -10mA,I <sub>B</sub> =0	-60		V
	BCP53			-80		
Base-emitter breakdown voltage		V <sub>(BR)EBO</sub>	I <sub>C</sub> = -10μΑ,I <sub>E</sub> =0	-5		V
Collector cut-off current		I <sub>CBO</sub>	V <sub>CB</sub> = -30 V, I <sub>E</sub> =0		-100	nA
		h <sub>FE(1)</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> =-5mA	25		
DC current gain		h <sub>FE(2)</sub>	V <sub>CE</sub> = -2V, I <sub>C</sub> =-150m A	63	250	
		h <sub>FE(3)</sub>	V <sub>CE</sub> = -2V, I <sub>C</sub> =-500m A	25		
Collector-emitter saturation voltage		V <sub>CE(sat)</sub>	I <sub>C</sub> =-500mA,I <sub>B</sub> =-50mA		-0.5	V
Base-emitter voltage		V <sub>BE</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> =-500m A		-1	V
Transition frequency		f⊤	V <sub>CE</sub> =-10V,I <sub>C</sub> =-50mA,f=100MHz	100		MHz

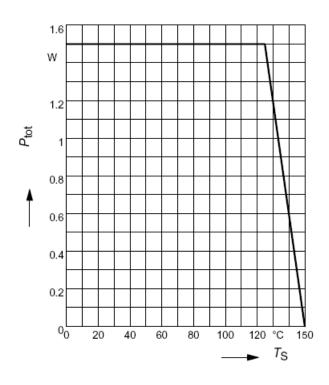
#### CLASSIFICATION OF hFE(2)

Rank	BCP51-10, BCP52-10, BCP53-10	BCP51-16, BCP52-16, BCP53-16		
<b>Range</b> 63-160		100-250		



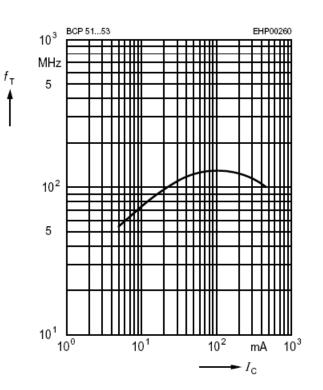
## **Typical Characteristics**

Total power dissipation  $P_{tot} = f(T_S)$ 



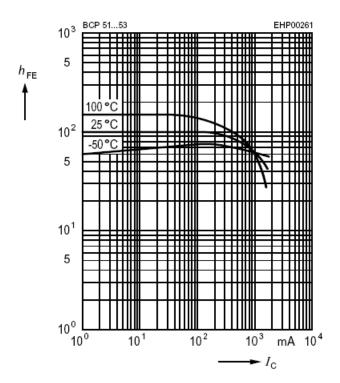
Transition frequency  $f_T = f(I_C)$ 

 $V_{CE} = 10V$ 



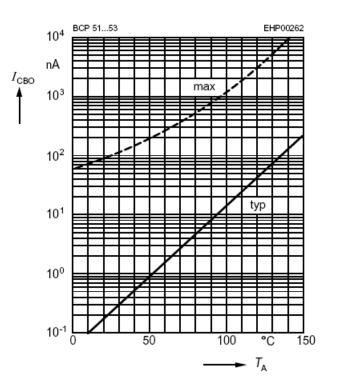
**DC** current gain  $hFE = f(I_C)$ 

VCE = 2V



Collector cutoff current  $I_{CBO} = f(T_A)$ 

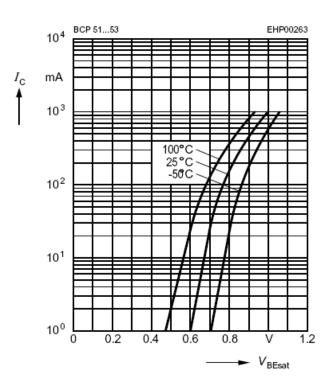
 $V_{CB} = 30V$ 





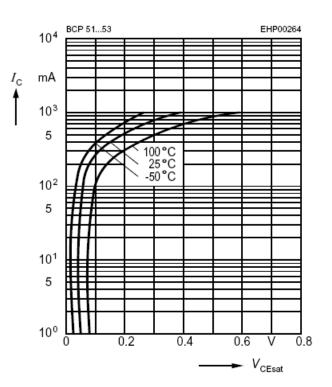
### Base-emitter saturation voltage

 $I_{\rm C} = f(V_{\rm BEsat}), h_{\rm FE} = 10$ 



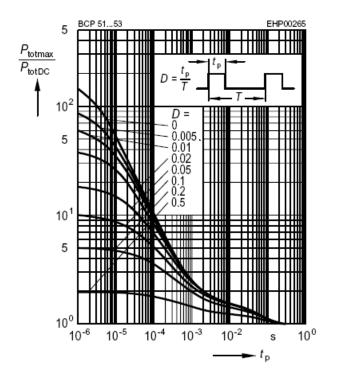
Collector-emitter saturation voltage

 $I_{\rm C} = f (V_{\rm CEsat}), h_{\rm FE} = 10$ 



### Permissible pulse load

 $P_{\text{totmax}} / P_{\text{totDC}} = f(t_p)$ 



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